

IN THE SPECIFICATION:

Please replace paragraph [0009] with the following amended paragraph:

[0009] The present invention generally provides low dielectric constant films and a method and apparatus for depositing low dielectric constant films. The method for depositing a low dielectric constant film on a substrate comprises providing a gas mixture to a deposition chamber, wherein the gas mixture comprises a silicon source, a carbon source, and $\text{NR}_1\text{R}_2\text{R}_3$ ~~into a chamber~~, wherein R_1 , R_2 , and R_3 are selected from the group consisting of alkyl and phenyl groups, and reacting the gas mixture while applying radio frequency (RF) power to form a nitrogen-containing silicon carbide layer on the substrate in the chamber. The gas mixture may also comprise an inert gas. The silicon source and the carbon source may be separate compounds or an organosilicon compound. In a preferred embodiment, the organosilicon compound has the general formula $\text{Si}_x\text{C}_y\text{H}_z$, wherein x has a range of 1 to 2, y has a range of 1 to 6, and z has a range of 4 to 18. A preferred nitrogen source having the formula $\text{NR}_1\text{R}_2\text{R}_3$ is trimethylamine.